DATA SHEET

2SC2673

Rev.E Mar.-2016

WR0<5 ṂṂ Ŀ QSQ æṀ ɥ s Ⅱ ᒣ Silicon NPN transistor in a TO-92 Plastic Package.

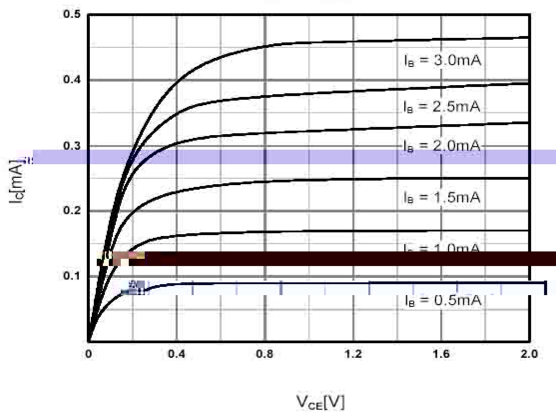
SF/

v ˝Ω Parameter	ɬ ᴺ Symbol	˝Ω Ӫ Rating	ᴅ Ʉ Unit
Collector to Base Voltage	V_{CBO}	40	V
Collector to Emitter Voltage	V_{CEO}	25	V
Emitter to Base Voltage	V_{EBO}	6.0	V
Collector Current - Continuous	I_C	1.5	A
Base Current - Continuous	I_B	500	mA
Collector Power Dissipation	P_C	1.0	W
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

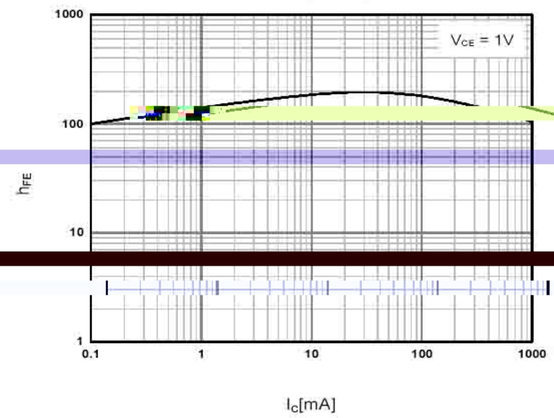
v ˝Ω Parameter	ɬ ᴺ Symbol	╜ ⁏ꜛ ꞇ Test Conditions	ῳ ṇ Ӫ Min	Ɛ ʒ Ӫ Typ	ῳ ᶾ Ӫ Max	ᴅ Ʉ Unit
Collector to Base Breakdown Voltage	V_{CBO}	I_C=0.1mA I_E=0	40			V
Collector to Emitter Breakdown Voltage	V_{CEO}	I_C=2.0mA I_B=0	25			V
Emitter to Base Breakdown Voltage	V_{EBO}	I_E=0.1mA I_C=0	6.0			V
Collector Cut-Off Current	I_{CBO}	V_{CB}=35V I_E=0			0.1	μA
Emitter Cut-Off Current	I_{EBO}	V_{EB}=6.0V I_C=0			0.1	μA
DC Current Gain	$h_{FE(1)}$	V_{CE}=1.0V I_C=100mA	200		350	
	$h_{FE(2)}$	V_{CE}=1.0V I_C=800mA	40			
	$h_{FE(3)}$	V_{CE}=1.0V I_C=5.0mA	45			▮
Collector-to-Emitter Saturation Voltage	$V_{CE(sat)}$	I_C				

/ Electrical Characteristic Curve

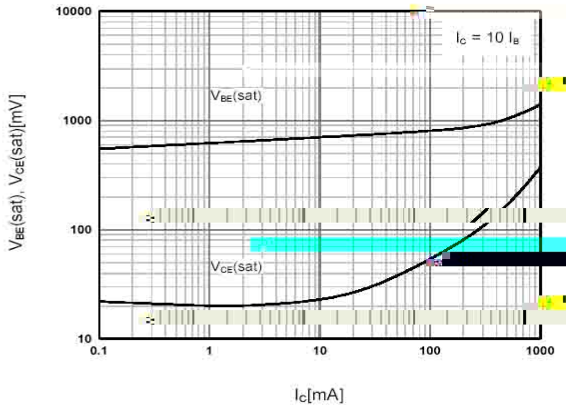
I_C – V_{CE}



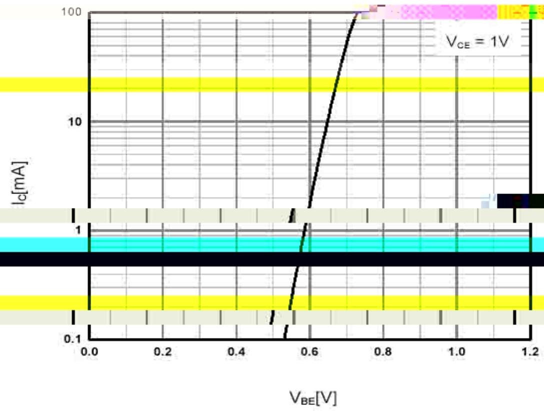
h_{FE} – I_C



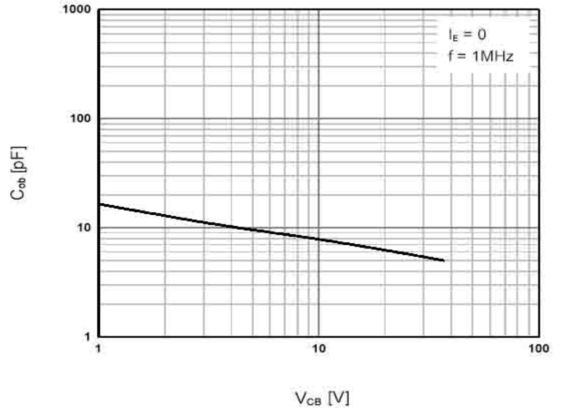
V_{CE}(sat) V_{BE}(sat) – I_C



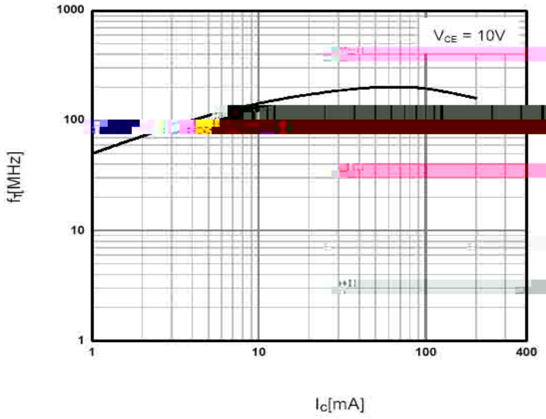
I_C – V_{BE}



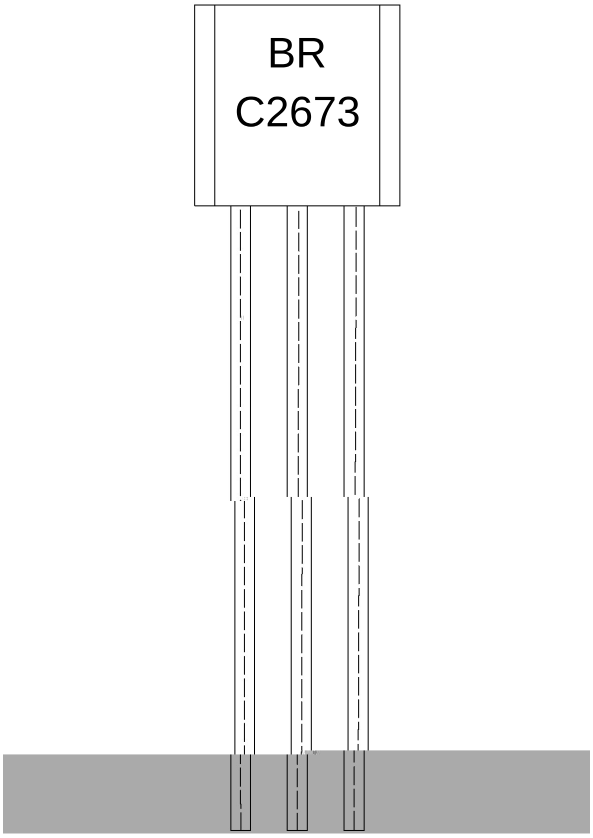
C_{ob} – V_{CB}



f_T – I_C



/ Marking Instructions



ب ˝ χ

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F59 : 6 χ	Ѭ ʒ ᴺ Ҧ
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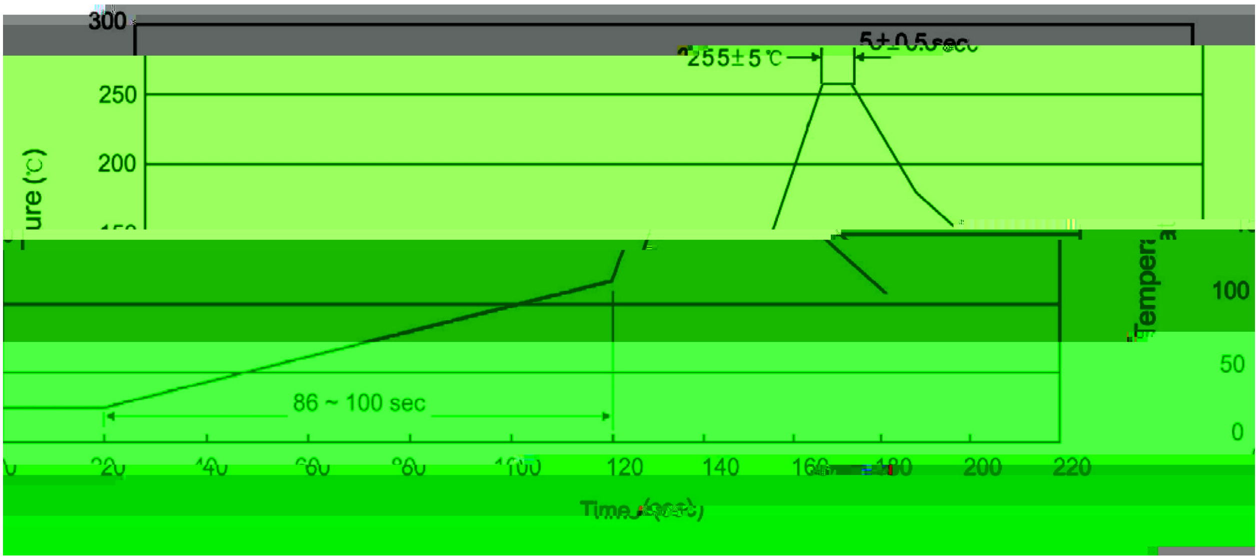
Note:

BR:	Company Code.
C2673:	Product Type.
****:	Lot No. Code,code change with Lot No.

( ) / Temperature Profile for Dip Soldering(Pb-Free)



ب ˝ χ	Note:
1 ỉ ♬ □ ẙ 25 Ḱ 150 ɫ ı ̀H ڑ 60 Ḱ 90sec;	1.Preheating:25~150 ɫ , Time:60~90sec.
2 Ś Ӫ □ ẙ 255 ° 5 ɫ ı ̀H ڑ ʽY ۸ ҧ 5 ° 0.5sec;	2.Peak Temp.:255 ° 5 ɫ , Duration:5 ° 0.5sec.
3 ì ˙ Ⴤ ˛ ɔ ھ ẙ ҧ 2 Ḱ 10 ɫ /sec.	3. Cooling Speed: 2~10 ɫ /sec.

/ Resistance to Soldering Heat Test Conditions

□ ẙ χ 270 ° 5 ɫ ̀H ڑ χ 10 ° 1 sec. Temp:270±5 Time:10±1 sec

/ Packaging SPEC.

̏Ω ţ γ Ŀ / BULK

Package Type	Units					Dimension		(unit mm3)

۸ Ṿ γ Ŀ / AMMO

Package Type	Units					Dimension	(unit mm3)

/ Notices